

IN THE CLAIMS:

Refined 1. (Currently Amended) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure composed of comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers and the thickness of said n-type clad layer is in a range of 100 Å to 500 Å, and

wherein said n-type clad layer is formed of a material substantially the same as said barrier layers, thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers.

Refined 2. (Canceled)

Refined 3. (Canceled)

Refined 4. (Original Claim) A group III nitride compound semiconductor light-emitting device according to claim 1, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer.

Refined 5. (Currently Amended) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $(0 < x < 1)$.

6. (Currently Amended) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $(0.01 \leq x \leq 0.05)$.

7. (Previously Added) The group III nitride compound semiconductor light-emitting device of claim 1, wherein said n-type clad layer and said barrier layers are formed of GaN.

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8. (Previously Added) The semiconductor light-emitting device of claim 1, wherein a thickness of said well layer is approximately 30 Å and a thickness of said barrier layer is approximately 70 Å.

9. (Currently Amended) The semiconductor light-emitting device of claim 1, further comprising:

a cap layer formed on said light-emitting layer, said cap layer being formed of a material substantially the same as said barrier layers; and

a p-type clad layer formed on and contacting said cap layer.

10. (Previously Added) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 180 Å to 500 Å, and a light emitted comprises green light in a wavelength range of approximately 510 nm to 530 nm.

11. (Previously Added) The semiconductor light-emitting device of claim 10, wherein said thickness of said p-type clad layer is in a range of approximately 240 Å to 360 Å.

12. (Previously Added) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 90 Å to 390 Å, and a light emitted comprises blue light in a wavelength range of approximately 460 nm to 475 nm.

13. (Previously Added) The semiconductor light-emitting device of claim 12, wherein said thickness of said p-type clad layer is in a range of approximately 120 Å to 300 Å.

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14. (Previously Added) The semiconductor light-emitting device of claim 9, wherein said p-type clad layer comprises p-type doped $\text{Al}_x\text{Ga}_{1-x}\text{N}$, where x ranges from approximately 0.10 to 0.14.

15. (Currently Amended) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure composed of comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,
wherein said n-type clad layer is made thicker than each of said barrier layers, said n-type clad layer is formed of a material substantially the same as said barrier layers, said material substantially the same thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers.

16. (New) The group III nitride compound semiconductor light-emitting device of claim 15, wherein said barrier layers comprise GaN.

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17. (New) The group III nitride compound semiconductor light-emitting device of claim 15, further comprising:

a cap layer in contact with said light-emitting layer on a side of said light-emitting layer opposite to that contacting said n-type clad layer, said cap layer being formed of a material substantially the same as said barrier layers.